

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

ECH8657 —

N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- 4V drive
- Halogen free compliance
- · Protection diode in

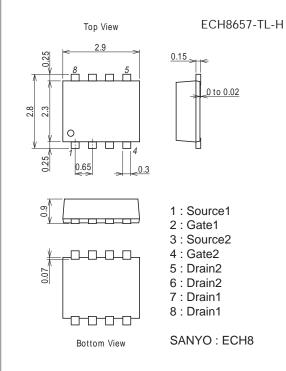
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		35	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ΙD		4.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	30	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	PT	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7011A-001



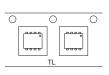
Product & Package Information

• Package : ECH8

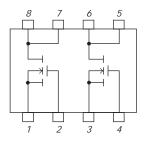
• JEITA, JEDEC : -

• Minimum Packing Quantity : 3,000 pcs./reel

Packing Type : TL



Electrical Connection



CH8

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TC

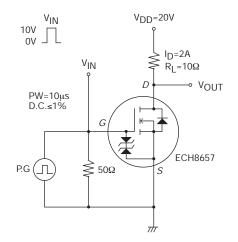
Marking



Electrical	Characteristics at Ta=25°C	
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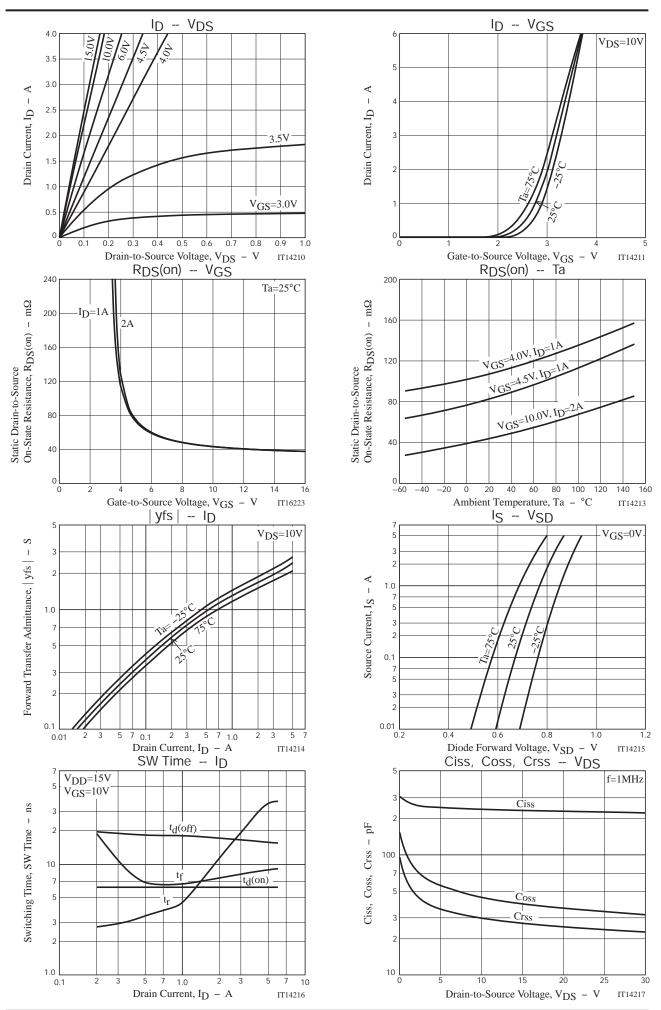
Deventer	Currels al	Conditions	Ratings				
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V	
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=35V$, $V_{GS}=0V$			1	μΑ	
Gate-to-Source Leakage Current	IGSS	$V_{GS}=\pm 16V, V_{DS}=0V$			±10	μΑ	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2A		1.66		S	
	R _{DS} (on)1	ID=2A, VGS=10V		45	59	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	ID=1A, VGS=4.5V		85	119	mΩ	
	R _{DS} (on)3	ID=1A, VGS=4V		110	155	mΩ	
Input Capacitance	Ciss			230		pF	
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		37		pF	
Reverse Transfer Capacitance	Crss]		25		рF	
Turn-ON Delay Time	t _d (on)			6		ns	
Rise Time	tr			11		ns	
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		17		ns	
Fall Time	tf]		9		ns	
Total Gate Charge	Qg			4.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =20V, V _{GS} =10V, I _D =4.5A		1.0		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		1.0		nC	
Diode Forward Voltage	V _{SD}	IS=4.5A, VGS=0V		0.85	1.2	V	

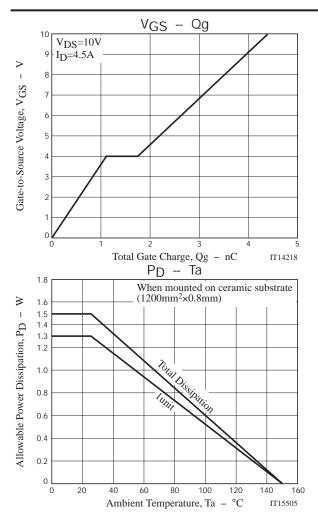
Switching Time Test Circuit

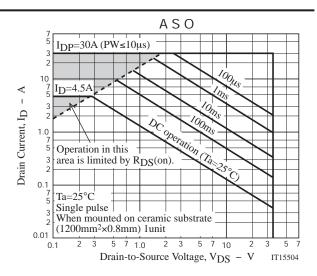


Ordering Information

Device Package		Shipping	memo	
ECH8657-TL-H ECH8		3,000pcs./reel	Pb Free and Halogen Free	







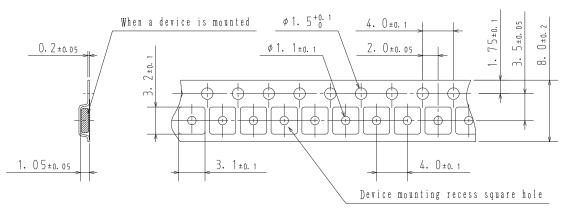
Embossed Taping Specification ECH8657-TL-H

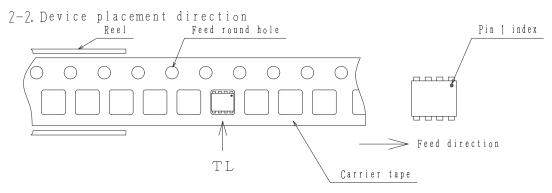
1. Packing Format

Package Name			imum Number of es contained (pcs)		Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1) Outer BOX (A-7)		
ECH8	CPH6	3,000	15,000	90,000	5 reels contained 6 inner boxes contained		
_	_				Dimensions:mm (external) Dimensions:mm (external)		
					183×72×185 440×195×210		
Packing method Reel label, Inner box label (unit:mm) Outer box label It is a label at the time of factory s The form of a label my change in phys distribution process, ⁰ TYPE No. LOT No. Quantity ⁶ 9 ¹⁰ TYPE 000000000 ¹⁰ TYPE 000000000 ¹⁰ TYPE 000000000 ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 QUOOD ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 QUOOD ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 QUOOD ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 QUOOD ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 QUOOD ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 QUOOD ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 QUOOD ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process, ¹⁰ TYPE 0000 PES 1 abel my change in phys distribution process,							

2. Taping configuration

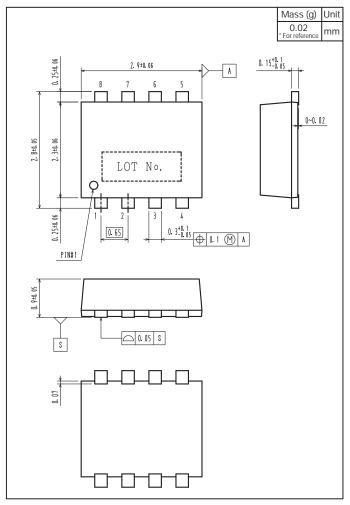
2-1. Carrier tape size (unit:mm)



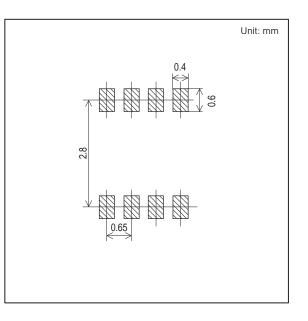


Those with pin 1 index on the feed hole side ·····TL

Outline Drawing ECH8657-TL-H



Land Pattern Example



Note on usage : Since the ECH8657 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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